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PATENT APPLICATION

03500.101486.

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



In re Application of:

TOMONARI NAKAYAMA, et al.

Application No.: 10/559,799

Int'l. Filing Date: June 9, 2005

For: FIELD EFFECT TRANSISTOR  
AND PRODUCTION PROCESS  
THEREOF

November 3, 2006

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In compliance with the duty of disclosure under 37 C.F.R. § 1.56 and in accordance with the practice under 37 C.F.R. §§ 1.97 and 1.98, the Examiner's attention is directed to the documents listed on the enclosed Form PTO-1449. Copies of the listed documents, other than the U.S. patent documents, are enclosed.

Japan 2004-63977, Japan 2004-63975, Japan 2004-128469, Japan 2004-6700, Japan 2004-146796, U.S. Patent No. 6,861,377, and U.S. Publication No. 2004/0131782 were cited in the International Search Report and/or Written Opinion which issued in the corresponding international application. A copy of the International Search Report and a copy of the Written Opinion are enclosed.

The following documents are discussed at the following pages of the specification:

<u>Documents</u>	<u>Page(s)</u>
A. Assadi, et al., Appl. Phys. Lett., Vol. 53, No. 3, July 18, 1988	2
H. Fuchigami, et al., Appl. Phys. Lett., Vol. 63, No. 10, September 6, 1993	2
Japan 10-190001	3
Janos Veres, et al., Advanced Functional Materials, Vol. 13, No. 3, March 2003	4
Zhenan Bao, et al., Chem. Mater., Vol. 9, No. 6, 1997	5

An English-language abstract for each of the Japanese documents listed on the Form PTO-1449 is enclosed.


According to a commercial database, U.S. Patent No. 6,861,377 is in the same patent family as Japan 2004-6700, U.S. Patent 6,107,117 is in the same patent family as Japan 10-190001, and U.S. Publication No. 2004/0131782 is in the same patent family as Japan 2004-146796.

This Information Disclosure Statement is being filed before the issuance of a first Office Action on the merits. Therefore, no fee under 37 C.F.R. § 1.97(c)(2) is believed due. Nevertheless, the Commissioner may charge Deposit Account No. 06-1205, should any fee be due for filing this paper.

Applicants request that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be initialed and returned indicating that such information has been considered.

Applicants' undersigned attorney may be reached in our Costa Mesa, California office at (714) 540-8700. All correspondence should continue to be directed to our below-listed address.

Respectfully submitted,

  
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U.S. DEPARTMENT OF COMMERCE  
PATENT AND TRADEMARK OFFICE  
LIST OF REFERENCES CITED BY APPLICANT(S)  
(Use several sheets if necessary)



ATTY DOCKET NO.  
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GROUP

U.S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	6,861,377	03/01/05	Hiral, et al.	438	781	
	6,107,117	08/22/00	Bao, et al.	438	99	
	2004/0131782	07/08/04	Hasei, et al.	427	337	

FOREIGN PATENT DOCUMENTS

	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES/NO/ OR ABSTRACT
	2004-146796	05/20/04	Japan			Abstract
	2004-128469	04/22/04	Japan			Abstract
	2004-63977	02/26/04	Japan			Abstract
	2004-63975	02/26/04	Japan			Abstract
	2004-6700	01/08/04	Japan			Abstract
	10-190001	07/21/98	Japan			Abstract

OTHER DOCUMENT(S) (Including Author, Title, Date, Pertinent Pages, Etc.)

	A. Assadi, et al., "Field-effect mobility of poly(3-hexylthiophene)", Appl. Phys. Lett., Vol. 53, No. 3, July 18, 1988, pp. 195-197.
	Zhenan Bao, et al., "High-Performance Plastic Transistors Fabricated by Printing Techniques", Chem. Mater., Vol. 9, No. 6, 1997, pp. 1299-1301.
	H. Fuchigami, et al., "Polythienylenevinylene thin-film transistor with high carrier mobility", Appl. Phys. Lett., Vol. 63, No. 10, September 6, 1993, pp. 1372-1374.
	Janos Veres, et al., "Low-k Insulators as the Choice of Dielectrics in Organic Field-Effect Transistors", Advanced Functional Materials, Vol. 13, No. 3, March 2003, pp. 199-204.
EXAMINER	DATE CONSIDERED

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Sheet 1 of 1